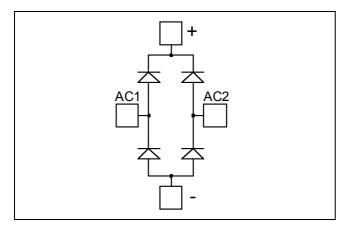


Diode Full Bridge Power Module

 $V_{RRM} = 1000V$ $I_C = 100A$ @ Tc = 70°C



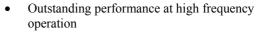
Application

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

Features

- Ultra fast recovery times
- Soft recovery characteristics
- High blocking voltage
- High current
- Low leakage current
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration

Benefits



- Low losses
- Low noise switching
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

All ratings @ $T_j = 25$ °C unless otherwise specified

Absolute maximum ratings

Symbol	Parameter			Max ratings	Unit
V_R	Maximum DC reverse Voltage			1000	V
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1000	V
т	Maximum Average Forward	Duta1 500/	$T_C = 25^{\circ}C$	130	A
$I_{F(AV)}$	Current	Duty cycle = 50%	$T_C = 70$ °C	100	
I _{F(RMS)}	RMS Forward Current	Duty cycle = 50%	$T_C = 45$ °C	130	71
I_{FSM}	Non-Repetitive Forward Surge Cu	rrent 8.3ms	$T_C = 45^{\circ}C$	500	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{F}	Diode Forward Voltage	$I_F = 100A$			2.1	2.7	V
		$I_F = 150A$			2.3		
		$I_F = 100A$	$T_{j} = 125^{\circ}C$		1.7		
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1000V$ $T_i = 25^{\circ}C$ $T_j = 125^{\circ}C$	$T_i = 25^{\circ}C$			100	4
			$T_{j} = 125^{\circ}C$			500	μΑ
C_{T}	Junction Capacitance	$V_R = 1000V$			120		pF

Dynamic Characteristics

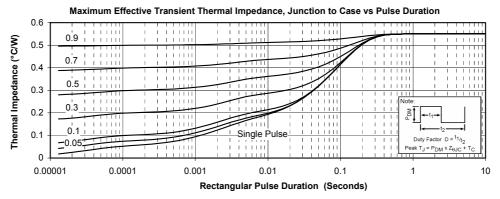
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
t_{rr}	Reverse Recovery Time	$I_F=1A, V_R=30V$ $di/dt = 100A/\mu s$	$T_j = 25^{\circ}C$		45		ns
t	Reverse Recovery Time		$T_j = 25^{\circ}C$		290		ns
t_{rr}	Reverse Recovery Time		$T_{j} = 125^{\circ}C$		340		115
Qrr	Reverse Recovery Charge	$I_F = 100A$ $V_R = 667V$	$T_j = 25^{\circ}C$		685		nC
Qrr	Reverse Recovery Charge	$di/dt = 200A/\mu s$	$T_{j} = 125^{\circ}C$		3645		пс
I_{RRM}	Reverse Recovery Current		$T_j = 25$ °C		6		A
	Reverse Recovery Current		$T_{\rm j} = 125^{\circ}{\rm C}$		18		Λ
t _{rr}	Reverse Recovery Time	$I_F = 100A \\ V_R = 667V \\ di/dt = 1000A/\mu s$			160		ns
Qrr	Reverse Recovery Charge		$T_j = 125$ °C		7100		nC
I_{RRM}	Reverse Recovery Current				70		Α

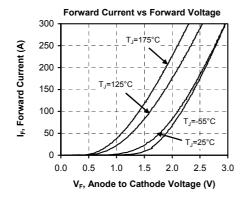
Thermal and package characteristics

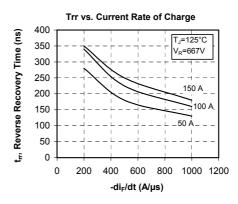
Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance					0.55	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	°C
T_{STG}	Storage Temperature Range			-40		125	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

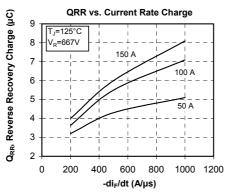


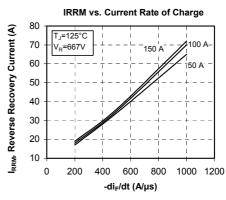
Typical Performance Curve

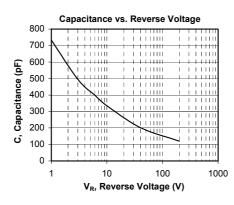


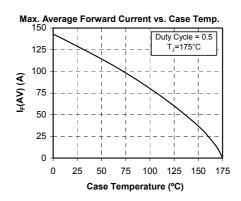






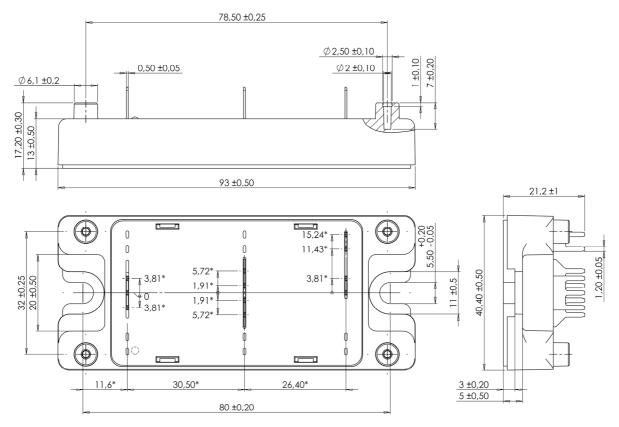








$SP4\ Package\ outline\ \ ({\rm dimensions\ in\ mm})$



ALL DIMENSIONS MARKED "*" ARE TOLERANCED AS : $\boxed{\Phi} \boxed{\emptyset} \ \ 1$



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